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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	I²C, IrDA, LINbus, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	50
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f411ret6tr

3.4 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

3.5 Embedded Flash memory

The devices embed up to 512 Kbytes of Flash memory available for storing programs and data.

To optimize the power consumption the Flash memory can also be switched off in Run or in Sleep mode (see *Section 3.18: Low-power modes*). Two modes are available: Flash in Stop mode or in DeepSleep mode (trade off between power saving and startup time, see *Table 34: Low-power mode wakeup timings(1)*). Before disabling the Flash memory, the code must be executed from the internal RAM.

One-time programmable bytes

A one-time programmable area is available with 16 OTP blocks of 32 bytes. Each block can be individually locked.

(Additional information can be found in the product reference manual.)

3.6 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.7 Embedded SRAM

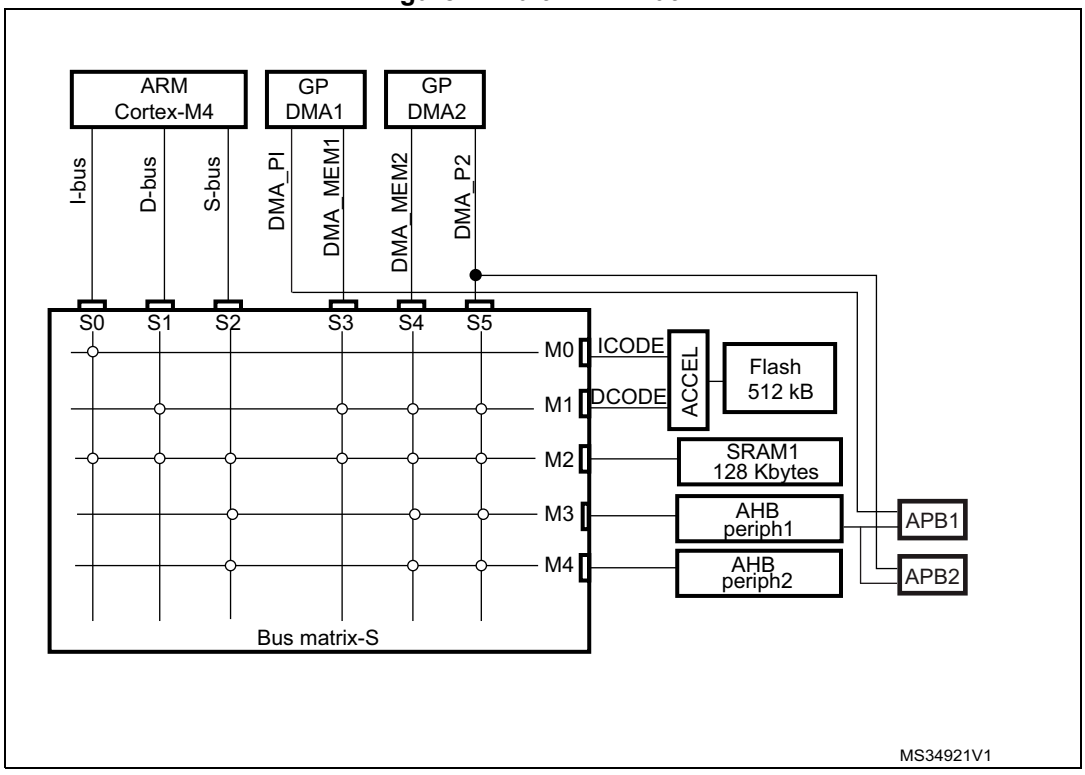
All devices embed:

- 128 Kbytes of system SRAM which can be accessed (read/write) at CPU clock speed with 0 wait states

3.8 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs) and the slaves (Flash memory, RAM, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

Figure 4. Multi-AHB matrix



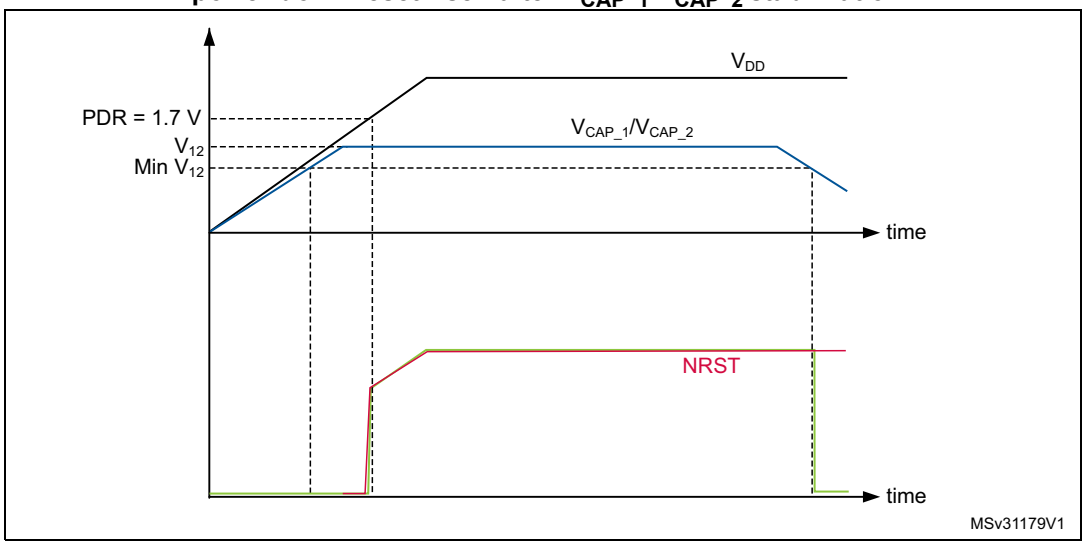
3.9 DMA controller (DMA)

The devices feature two general-purpose dual-port DMAs (DMA1 and DMA2) with 8 streams each. They are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. They feature dedicated FIFOs for APB/AHB peripherals, support burst transfer and are designed to provide the maximum peripheral bandwidth (AHB/APB).

The two DMA controllers support circular buffer management, so that no specific code is needed when the controller reaches the end of the buffer. The two DMA controllers also have a double buffering feature, which automates the use and switching of two memory buffers without requiring any special code.

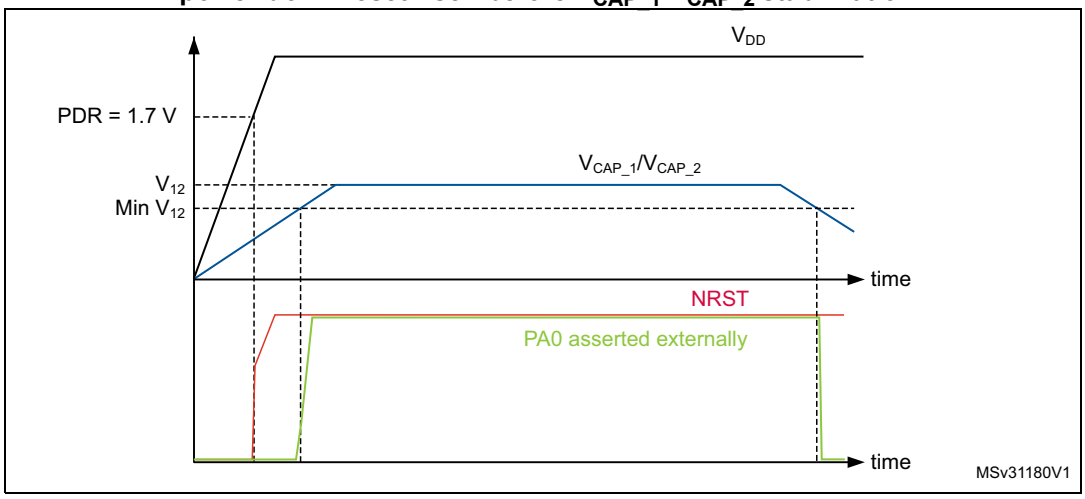
Each stream is connected to dedicated hardware DMA requests, with support for software trigger on each stream. Configuration is made by software and transfer sizes between source and destination are independent.

Figure 7. Startup in regulator OFF: slow V_{DD} slope - power-down reset risen after V_{CAP_1}/V_{CAP_2} stabilization



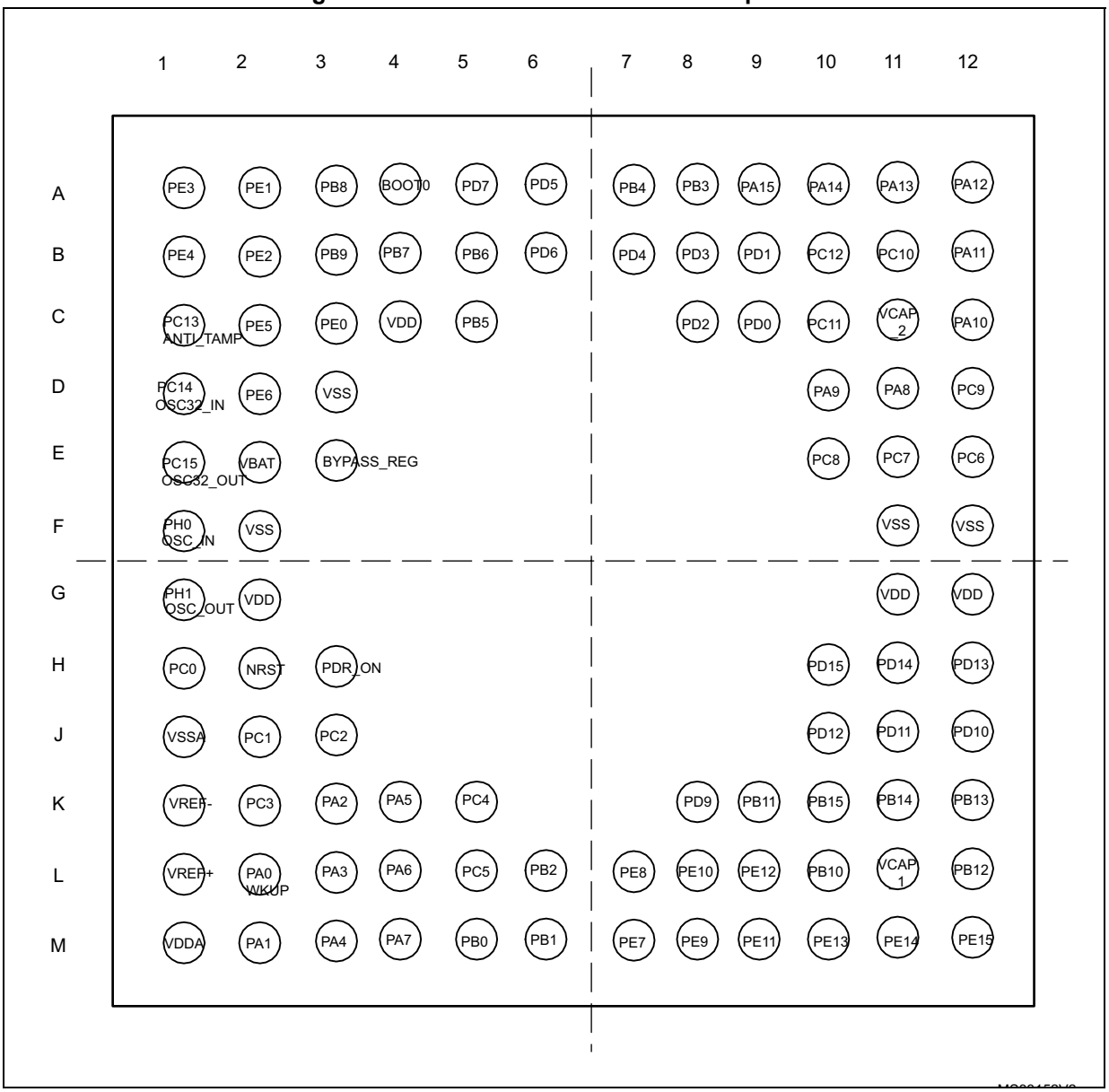
1. This figure is valid whatever the internal reset mode (ON or OFF).

Figure 8. Startup in regulator OFF mode: fast V_{DD} slope - power-down reset risen before V_{CAP_1}/V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).

Figure 13. STM32F411xC/xE UFBGA100 pinout



1. This figure shows the package top view

Table 8. STM32F411xC/xE pin definitions (continued)

Pin number					Pin name (function after reset)(1)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP49	LQFP100	UFBGA100						
31	43	C2	69	C12	PA10	I/O	FT	-	TIM1_CH3, SPI5_MOSI/I2S5_SD, USART1_RX, USB_FS_ID, EVENTOUT	-
32	44	C1	70	B12	PA11	I/O	FT	-	TIM1_CH4, SPI4_MISO, USART1_CTS, USART6_TX, USB_FS_DM, EVENTOUT	-
33	45	C3	71	A12	PA12	I/O	FT	-	TIM1_ETR, SPI5_MISO, USART1_RTS, USART6_RX, USB_FS_DP, EVENTOUT	-
34	46	B3	72	A11	PA13	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-
-	-	-	73	C11	VCAP_2	S	-	-	-	-
35	47	B1	74	F11	VSS	S	-	-	-	-
36	48	B2	75	G11	VDD	S	-	-	-	-
37	49	A1	76	A10	PA14	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
38	50	A2	77	A9	PA15	I/O	FT	-	JTDI, TIM2_CH1/TIM2_ETR, SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, USART1_TX, EVENTOUT	-
-	51	-	78	B11	PC10	I/O	FT	-	SPI3_SCK/I2S3_CK, SDIO_D2, EVENTOUT	-
-	52	-	79	C10	PC11	I/O	FT	-	I2S3ext_SD, SPI3_MISO, SDIO_D3, EVENTOUT	-
-	53	-	80	B10	PC12	I/O	FT	-	SPI3_MOSI/I2S3_SD, SDIO_CK, EVENTOUT	-

Table 15. Features depending on the operating power supply range (continued)

Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ($f_{Flashmax}$)	Maximum Flash memory access frequency with wait states (1)(2)	I/O operation	Clock output frequency on I/O pins(3)	Possible Flash memory operations
V_{DD} = 2.4 to 2.7 V	Conversion time up to 2.4 Msps	24 MHz	100 MHz with 4 wait states	– I/O compensation works	up to 50 MHz	16-bit erase and program operations
V_{DD} = 2.7 to 3.6 V(6)	Conversion time up to 2.4 Msps	30 MHz	100 MHz with 3 wait states	– I/O compensation works	– up to 100 MHz when V_{DD} = 3.0 to 3.6 V – up to 50 MHz when V_{DD} = 2.7 to 3.0 V	32-bit erase and program operations

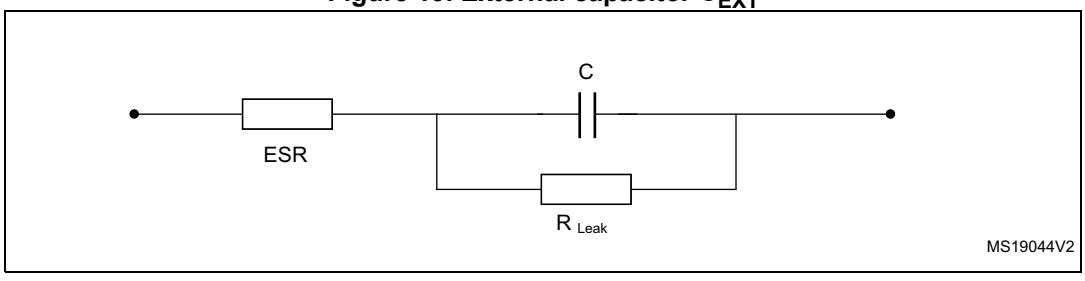
1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.
3. Refer to *Table 55: I/O AC characteristics* for frequencies vs. external load.
4. V_{DD}/V_{DDA} minimum value of 1.7 V, with the use of an external power supply supervisor (refer to *Section 3.15.2: Internal reset OFF*).
5. Prefetch is not available. Refer to AN3430 application note for details on how to adjust performance and power.
6. The voltage range for the USB full speed embedded PHY can drop down to 2.7 V. However the electrical characteristics of D- and D+ pins will be degraded between 2.7 and 3 V.

6.3.2 VCAP_1/VCAP_2 external capacitors

Stabilization for the main regulator is achieved by connecting the external capacitor C_{EXT} to the VCAP_1 and VCAP_2 pins. For packages supporting only 1 VCAP pin, the 2 CEXT capacitors are replaced by a single capacitor.

C_{EXT} is specified in *Table 16*.

Figure 19. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance.

Table 16. VCAP_1/VCAP_2 operating conditions(1)

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor with a single VCAP pin available	4.7 µF
ESR	ESR of external capacitor with a single VCAP pin available	< 1 Ω

1. When bypassing the voltage regulator, the two 2.2 µF V_{CAP} capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

6.3.3 Operating conditions at power-up/power-down (regulator ON)

Subject to general operating conditions for T_A.

Table 17. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	µs/V
	V_{DD} fall time rate	20	∞	

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A.

Table 18. Operating conditions at power-up / power-down (regulator OFF)(1)

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	µs/V
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when V_{DD} reach below 1.08 V.

Note: This feature is only available for UFBGA100 package.

Table 23. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory - V_{DD} = 3.6 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)				Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD}	Supply current in **Run mode**	External clock, PLL ON(2), all peripherals enabled(3)(4)	100	20.7	22.2	22.5	23.2	24.4	mA
			84	16.8	18.0	18.3	19.0	20.1	
			64	11.8	12.7	12.9	13.6	14.6	
			50	9.3	10.2	10.4	11.1	12.0	
			20	4.8	5.5	5.8	6.5	7.4	
		HSI, PLL OFF(2), all peripherals enabled(3)	16	3.0	3.3	3.8	4.5	5.4	
			1	0.7	1.0	1.4	2.1	3.0	
		External clock, PLL ON(2) all peripherals disabled(3)	100	11.6	12.6	12.9	13.6	14.8	
			84	9.7	10.2(5)	11.1	11.3	12.5	
			64	6.7	7.4	7.7	8.3	9.4	
			50	5.4	6.0	6.3	7.0	8.0	
			20	2.9	3.4	3.7	4.4	5.4	
		HSI, PLL OFF(2), all peripherals disabled(3)	16	1.9	2.2	2.6	3.3	4.3	
			1	0.7	0.9	1.3	2.1	3.1	

1. Guaranteed by characterization results.
2. Refer to *Table 41* and RM0383 for the possible PLL VCO setting
3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
4. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.
5. Guaranteed by test in production.

Table 24. Typical and maximum current consumption in run mode, code with data processing (ART accelerator disabled) running from Flash memory - V_{DD} = 3.6 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)				Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD}	Supply current in **Run mode**	External clock, PLL ON(2), all peripherals enabled(3)(4)	100	29.5	31.5	32.3	33.3	34.7	mA
			84	25.5	27.1	27.9	28.9	30.2	
			64	18.6	19.8	20.4	21.2	22.4	
			50	15.2	16.4	16.9	17.7	18.7	
			20	7.6	8.4	8.8	9.5	10.5	
		HSI, PLL OFF(2), all peripherals enabled(3)	16	4.8	5.2	5.7	6.5	7.5	
			1	0.9	1.3	1.6	2.4	3.4	
		External clock, PLL ON(2) all peripherals disabled(3)	100	20.4	21.8	22.7	23.8	25.1	
			84	18.4	19.2(5)	20.9	21.1	22.4	
			64	13.5	14.5	15.2	15.9	17.2	
			50	11.3	12.2	12.8	13.6	14.7	
			20	5.6	6.4	6.7	7.4	8.5	
		HSI, PLL OFF(2), all peripherals disabled(3)	16	3.6	4.1	4.5	5.2	6.3	
			1	0.9	1.2	1.6	2.3	3.4	

1. Guaranteed by characterization results.
2. Refer to *Table 41* and RM0383 for the possible PLL VCO setting
3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
4. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.
5. Guaranteed by test in production.

Figure 28 and *Figure 29* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 28. PLL output clock waveforms in center spread mode

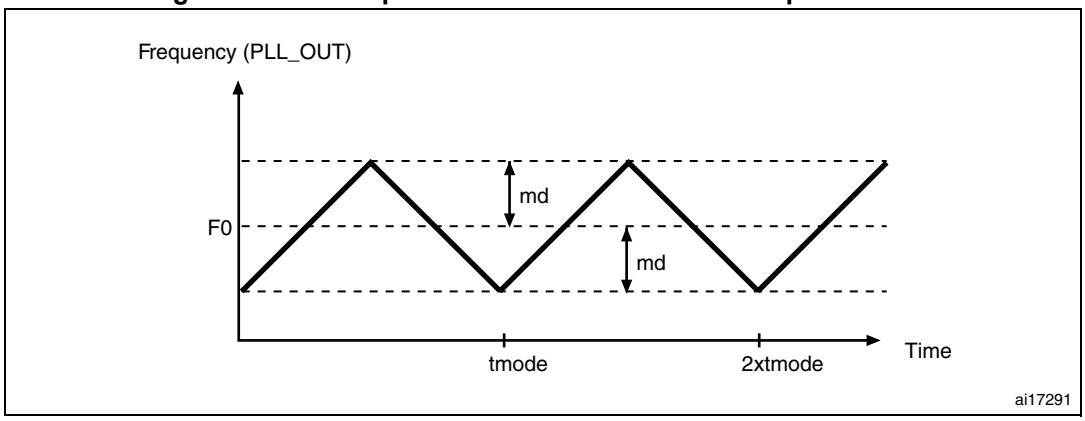
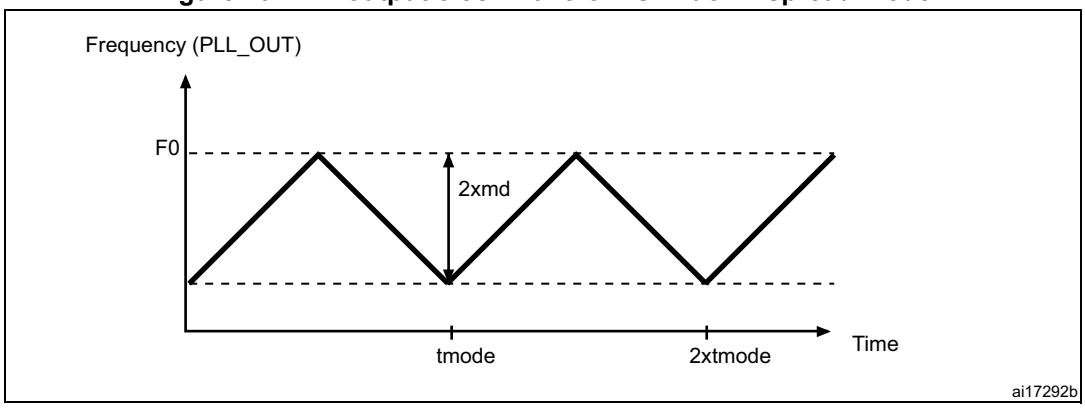


Figure 29. PLL output clock waveforms in down spread mode



6.3.12 Memory characteristics

Flash memory

The characteristics are given at T_A = - 40 to 125 °C unless otherwise specified.

The devices are shipped to customers with the Flash memory erased.

Table 44. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DD}	Supply current	Write / Erase 8-bit mode, V_{DD} = 1.7 V	-	5	-	mA
		Write / Erase 16-bit mode, V_{DD} = 2.1 V	-	8	-	
		Write / Erase 32-bit mode, V_{DD} = 3.3 V	-	12	-	

Table 53. I/O static characteristics (continued)

Symbol	Parameter		Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor(6)	All pins except for PA10 (OTG_FS_ID)	$V_{IN} = V_{SS}$	30	40	50	kΩ
		PA10 (OTG_FS_ID)	-	7	10	14	
R_{PD}	Weak pull-down equivalent resistor(7)	All pins except for PA10 (OTG_FS_ID)	$V_{IN} = V_{DD}$	30	40	50	
		PA10 (OTG_FS_ID)	-	7	10	14	
C_{IO}(8)	I/O pin capacitance		-	-	5	-	pF

1. Guaranteed by test in production.
2. Guaranteed by design.
3. With a minimum of 200 mV.
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to *Table 52: I/O current injection susceptibility*
5. To sustain a voltage higher than VDD +0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins.Refer to *Table 52: I/O current injection susceptibility*
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
8. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

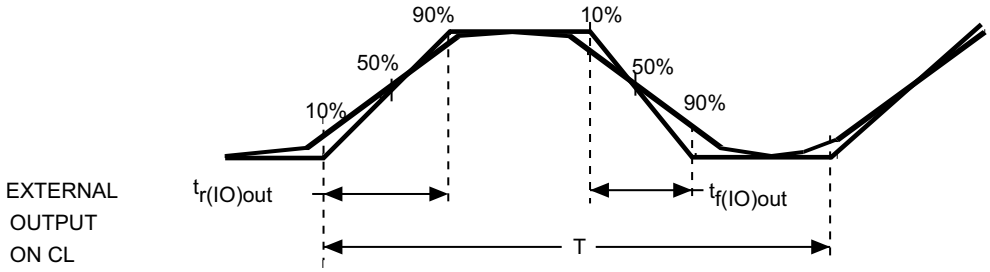
All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT and TC I/Os is shown in *Figure 30*.

Table 55. I/O AC characteristics[1][2] (continued)

OSPEEDRy [1:0] bit value[1]	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
11	$F_{max(IO)out}$	Maximum frequency[3]	C_L = 30 pF, V_{DD} ≥ 2.70 V	-	-	100[4]	MHz
			C_L = 30 pF, V_{DD} ≥ 1.7 V	-	-	50[4]	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 30 pF, V_{DD} ≥ 2.70 V	-	-	4	ns
			C_L = 30 pF, V_{DD} ≥ 1.7 V	-	-	6	
			C_L = 10 pF, V_{DD}≥ 2.70 V	-	-	2.5	
			C_L = 10 pF, V_{DD}≥ 1.7 V	-	-	4	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller		10	-	-	ns

1. Guaranteed by characterization results.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in *Figure 31*.
4. For maximum frequencies above 50 MHz and V_{DD} > 2.4 V, the compensation cell should be used.

Figure 31. I/O AC characteristics definition



Maximum frequency is achieved if (t_r + t_f) ≤ (2/3)T and if the duty cycle is (45-55%) when loaded by CL specified in the table " *I/O AC characteristics*".

ai14131d

6.3.17 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 53*).

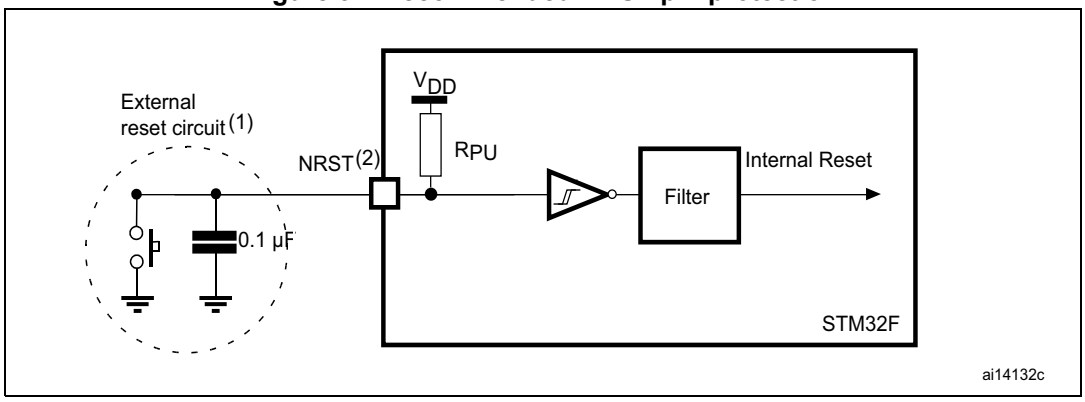
Unless otherwise specified, the parameters given in *Table 56* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*. Refer to *Table 53: I/O static characteristics* for the values of VIH and VIL for NRST pin.

Table 56. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor(1)	$V_{IN} = V_{SS}$	30	40	50	kΩ
$V_{F(NRST)}$(2)	NRST Input filtered pulse		-	-	100	ns
$V_{NF(NRST)}$(2)	NRST Input not filtered pulse	$V_{DD} > 2.7$ V	300	-	-	ns
T_{NRST_OUT}	Generated reset pulse duration	Internal Reset source	20	-	-	µs

1. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).
2. Guaranteed by design.

Figure 32. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 56*. Otherwise the reset is not taken into account by the device.

SPI interface characteristics

Unless otherwise specified, the parameters given in *Table 60* for the SPI interface are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 14*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to *Section 6.3.16: I/O port characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

Table 60. SPI dynamic characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master full duplex/receiver mode, 2.7 V < V_{DD} < 3.6 V SPI1/4/5	-	-	42	MHz
		Master full duplex/receiver mode, 3.0 V < V_{DD} < 3.6 V SPI1/4/5	-	-	50	
		Master transmitter mode 1.7 V < V_{DD} < 3.6 V SPI1/4/5	-	-	50	
		Master mode 1.7 V < V_{DD} < 3.6 V SPI1/2/3/4/5	-	-	25	
		Slave transmitter/full duplex mode 2.7 V < V_{DD} < 3.6 V SPI1/4/5	-	-	38(2)	
		Slave receiver mode, 1.8 V < V_{DD} < 3.6 V SPI1/4/5	-	-	50	
		Slave mode, 1.8 V < V_{DD} < 3.6 V SPI1/2/3/4/5	-	-	25	
Duty(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode, SPI presc = 2	T_{PCLK}-1.5	T_{PCLK}	T_{PCLK} +1.5	ns
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	$3T_{PCLK}$	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	$2T_{PCLK}$	-	-	ns
$t_{su(MI)}$	Data input setup time	Master mode	4	-	-	ns
$t_{su(SI)}$		Slave mode	2.5	-	-	ns
$t_{h(MI)}$	Data input hold time	Master mode	7.5	-	-	ns
$t_{h(SI)}$		Slave mode	3.5	-	-	ns

6.3.25 RTC characteristics

Table 77. Dynamic characteristics: eMMC characteristics V_{DD} = 1.7 V to 1.9 V(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp = 50 MHz	10	10.5	-	ns
$t_{W(CKH)}$	Clock high time	fpp = 50 MHz	9	9.5	-	
CMD, D inputs (referenced to CK) in eMMC mode						
t_{ISU}	Input setup time HS	fpp = 50 MHz	0	-	-	ns
t_{IH}	Input hold time HS	fpp = 50 MHz	6	-	-	
CMD, D outputs (referenced to CK) in eMMC mode						
t_{OV}	Output valid time HS	fpp = 50 MHz	-	3.5	5	ns
t_{OH}	Output hold time HS	fpp = 50 MHz	2	-	-	

1. Guaranteed by characterization results.
2. C_{load} = 20 pF

Table 78. RTC characteristics

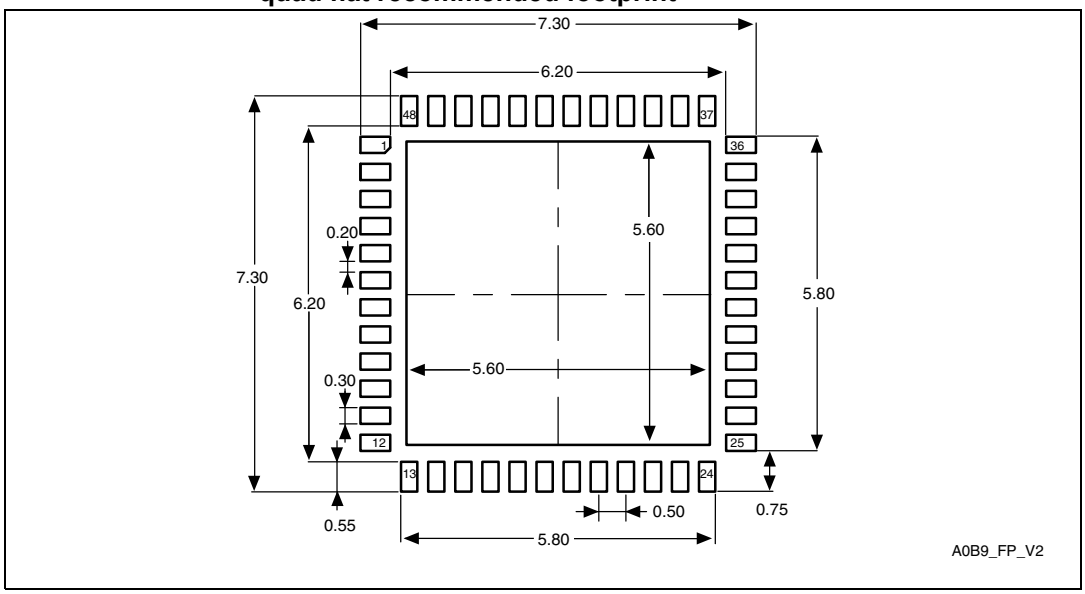
Symbol	Parameter	Conditions	Min	Max
-	f_{PCLK1}/RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

Table 81. UFQFPN48 - 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
T	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
e	-	0.500	-	-	0.0197	-
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

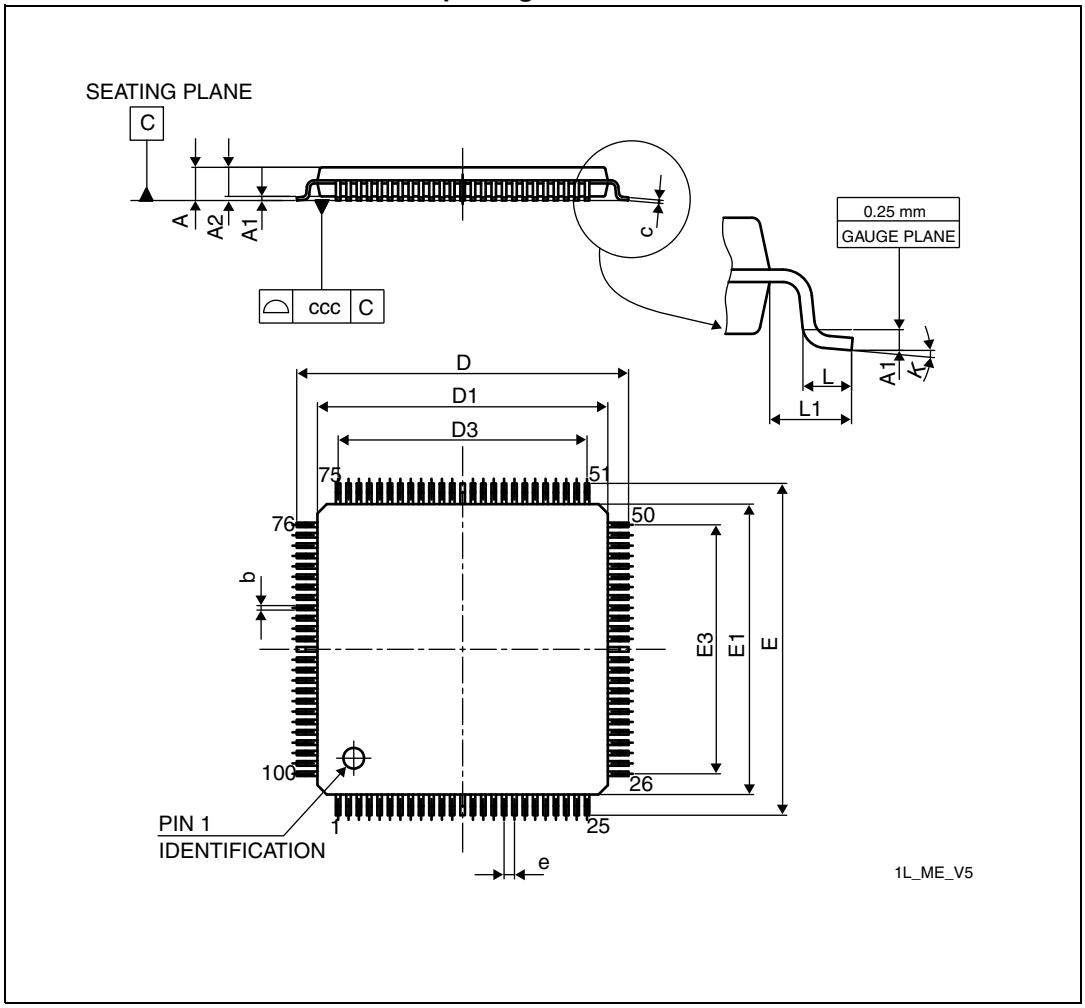
Figure 50. UFQFPN48 - 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat recommended footprint



1. Dimensions are in millimeters.

7.4 LQFP100 package information

Figure 55. LQFP100 - 100-pin, 14 x 14 mm, 100-pin low-profile quad flat package outline



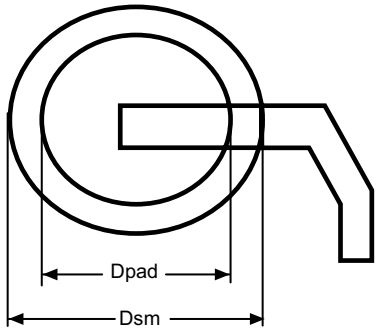
1. Drawing is not to scale.

Table 84. UFBGA100, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
ddd	-	-	0.100	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 59. Recommended PCB design rules for pads (0.5 mm-pitch BGA)



Pitch	0.5 mm
D pad	0.27 mm
Dsm	0.35 mm typ (depends on the soldermask registration tolerance)
Solder paste	0.27 mm aperture diameter

ai15495

1. Non solder mask defined (NSMD) pads are recommended.
2. 4 to 6 mils solder paste screen printing process.

B.2 Sensor Hub application example

Figure 64. Sensor Hub application example